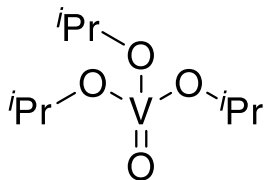


Catalog # 23-5000 Vanadium (V) tri-i-propoxy oxide, 98+% VTIP



Thermal Behavior:

- Boiling Point: 102°C/9 Torr [1], 80-82°C/2 Torr
- Melting Point: -14--11°C
- Vapor pressure: 0.29 Torr/45 °C [3]

Technical Notes:

1. ALD/CVD precursor for vanadium containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
V ₂ O ₅	ALD	90-110°C	7.5-22.5 Torr	O ₂	90-160°C	2
	ALD	45°C	-	H ₂ O	105°C	3-4
	PE-ALD	40°C	-	^{PL} H ₂ O; ^{PL} O ₂	50-300°C	5
	ALD	-	-	H ₂ O ₂	100°C	6
	ALD	45°C	-	O ₃	150-210°C	7
Bi:V ₂ O ₅	ALD	45°C	-	BiPh ₃ , O ₃	130°C	8
	ALD	45°C	-	BiPh ₃ , H ₂ O/ROH	130°C	9

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